

4V Drive Nch + Nch MOSFET

QS8K21

Structure

Silicon N-channel MOSFET

Features

- 1) Low on-resistance.
- 2) High power package(TSMT8).
- 3) Low voltage drive(4V drive).

Application

Switching

Packaging specifications

	Package	Taping
Туре	Code	TR
	Basic ordering unit (pieces)	3000
QS8K21		0

● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	45	V
Gate-source voltage		V_{GSS}	<u>+</u> 20	V
Drain current	Continuous	I _D	<u>±</u> 4	Α
	Pulsed	I _{DP} *1	±12	Α
Source current	Continuous	l _s	1	Α
(Body Diode)	Pulsed	I _{sp} *1	12	Α
Power dissipation		P _D *2	1.5	W / TOTAL
		I D -	1.25	W / ELEMENT
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

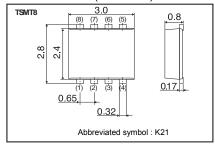
^{*1} Pw≤10µs, Duty cycle≤1%

● Thermal resistance

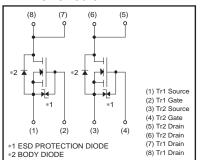
- Morman resistance							
Parameter	Symbol	Limits	Unit				
Channel to Ambient	Rth (ch-a)	83.3	°C / W /TOTAL				
Chariner to Ambient	Kill (Cli-a)	100	C / W /ELEMENT				

^{*}Mounted on a ceramic board.

● Dimensions (Unit : mm)



• Inner circuit



^{*2} Mounted on a ceramic board.

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●Electrical characteristics (Ta = 25°C)

<It is the same ratings for Tr1 and Tr2.>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	ı	-	±10	μA	V_{GS} =±20V, V_{DS} =0V
Drain-source breakdown voltage	V _{(BR)DSS}	45	-	-	٧	I _D =1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	1	-	1	μA	V_{DS} =45V, V_{GS} =0V
Gate threshold voltage	V _{GS (th)}	1.0	-	2.5	٧	V_{DS} =10V, I_{D} =1mA
0	*	1	38	53		I _D =4A, V _{GS} =10V
Static drain-source on-state resistance	R _{DS (on)}	1	48	67	mΩ	I _D =4A, V _{GS} =4.5V
		1	53	75		I _D =4A, V _{GS} =4.0V
Forward transfer admittance	I Y _{fs} I*	2		-	S	I _D =4A, V _{DS} =10V
Input capacitance	C_{iss}	-	460	-	pF	V _{DS} =10V
Output capacitance	C _{oss}	-	110	-	pF	V _{GS} =0V
Reverse transfer capacitance	C_{rss}	-	55	-	pF	f=1MHz
Turn-on delay time	t _{d(on)} *	ı	9	-	ns	I _D =2A, V _D 5 25V
Rise time	t _r *	1	25	-	ns	V _{GS} =10V
Turn-off delay time	$t_{d(off)}^*$	1	30	-	ns	R _L ≒12.5Ω
Fall time	t _f *	-	7	-	ns	R_G =10 Ω
Total gate charge	Q _g *	-	5.4	-	nC	I _D =4A, V _D 5 25V
Gate-source charge	Q _{gs} *	ı	2.0	-	nC	V _{GS} =5V R ; 6.3Ω
Gate-drain charge	Q _{gd} *	1	1.6	-	nC	R_G =10 Ω

^{*}Pulsed

●Body diode characteristics (Source-Drain) (Ta = 25°C)

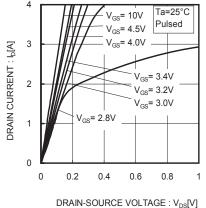
<It is the same ratings for Tr1 and Tr2.>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward Voltage	V _{SD} *	-	-	1.2	V	I _s =4A, V _{GS} =0V

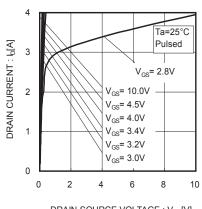
^{*}Pulsed

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Electrical characteristics curves



DRAIN-SOURCE VOLTAGE . V_{DS[}V]



DRAIN-SOURCE VOLTAGE : V_{DS}[V]

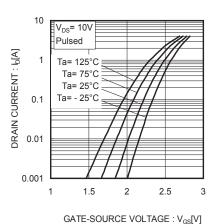
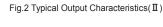


Fig.3 Typical Transfer Characteristics





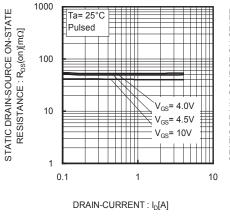


Fig.4 Static Drain-Source On-State
Resistance vs. Drain Current(I)

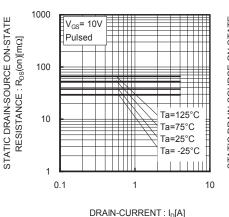
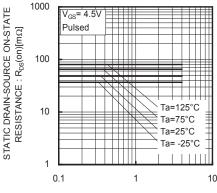


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(II)



DRAIN-CURRENT : I_D[A]

Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(Ⅲ)

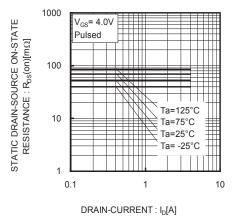


Fig.7 Static Drain-Source On-State
Resistance vs. Drain Current(IV)

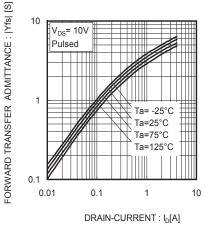


Fig.8 Forward Transfer Admittance vs. Drain Current

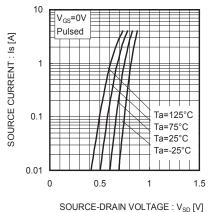
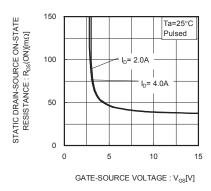
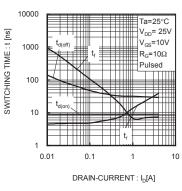


Fig.9 Reverse Drain Current
vs. Sourse-Drain Voltage

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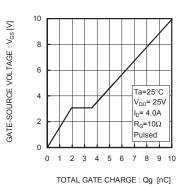


Fig.10 Static Drain-Source On-State Resistance vs. Gate Source Voltage

Fig.11 Switching Characteristics

Fig.12 Dynamic Input Characteristics

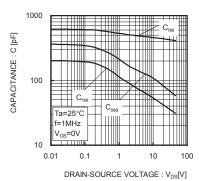


Fig.13 Typical Capacitance vs. Drain-Source Voltage

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●Measurement circuits

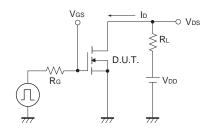


Fig.1-1 Switching time measurement circuit

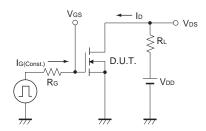


Fig.2-1 Gate charge measurement circuit

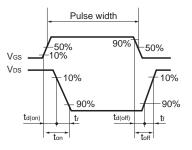


Fig.1-2 Switching waveforms

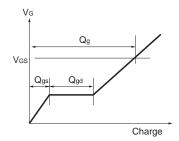


Fig.2-2 Gate charge waveform

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